

Growth of epitaxial silicon nanowires on a Si substrate by a metal-catalyst-free process

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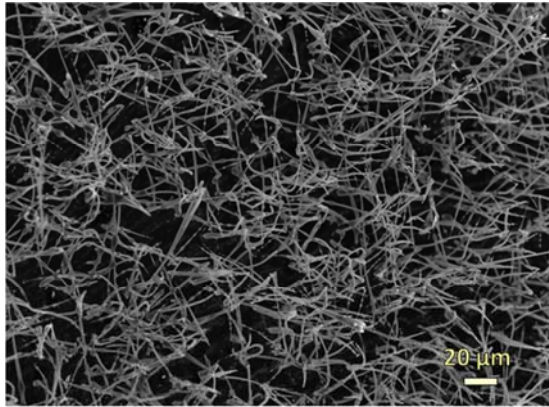


Fig. S1. SEM image of nanowires grown at 30 Pa. The growth of bent nanowires with high oxygen contents is more dominant because residual oxygen in the quartz capsule is incorporated into nanowires.